



Welcome to [E-XFL.COM](https://www.e-xfl.com)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100lkafb-v0

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13					
			20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128 KB	8 KB	12 KB	—	—	—	R5F100AG	R5F100BG	R5F100CG
	—		—	—	—	R5F101AG	R5F101BG	R5F101CG
96 KB	8 KB	8 KB	—	—	—	R5F100AF	R5F100BF	R5F100CF
	—		—	—	—	R5F101AF	R5F101BF	R5F101CF
64 KB	4 KB	4 KB Note	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
	—		R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48 KB	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
	—		R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32 KB	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
	—		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16 KB	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
	—		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash ROM	Data flash	RAM	RL78/G13							
			40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512 KB	8 KB	32 KB Note	—	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
	—		—	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384 KB	8 KB	24 KB	—	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
	—		—	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256 KB	8 KB	20 KB Note	—	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
	—		—	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192 KB	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
	—		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128 KB	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	—
	—		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	—
96 KB	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	—
	—		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	—
64 KB	4 KB	4 KB Note	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	—	—	—
	—		R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	—	—	—
48 KB	4 KB	3 KB Note	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	—	—	—
	—		R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	—	—	—
32 KB	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	—	—	—
	—		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	—	—	—
16 KB	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	—	—	—	—	—
	—		R5F101EA	R5F101FA	R5F101GA	—	—	—	—	—

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Table 1-1. List of Ordering Part Numbers

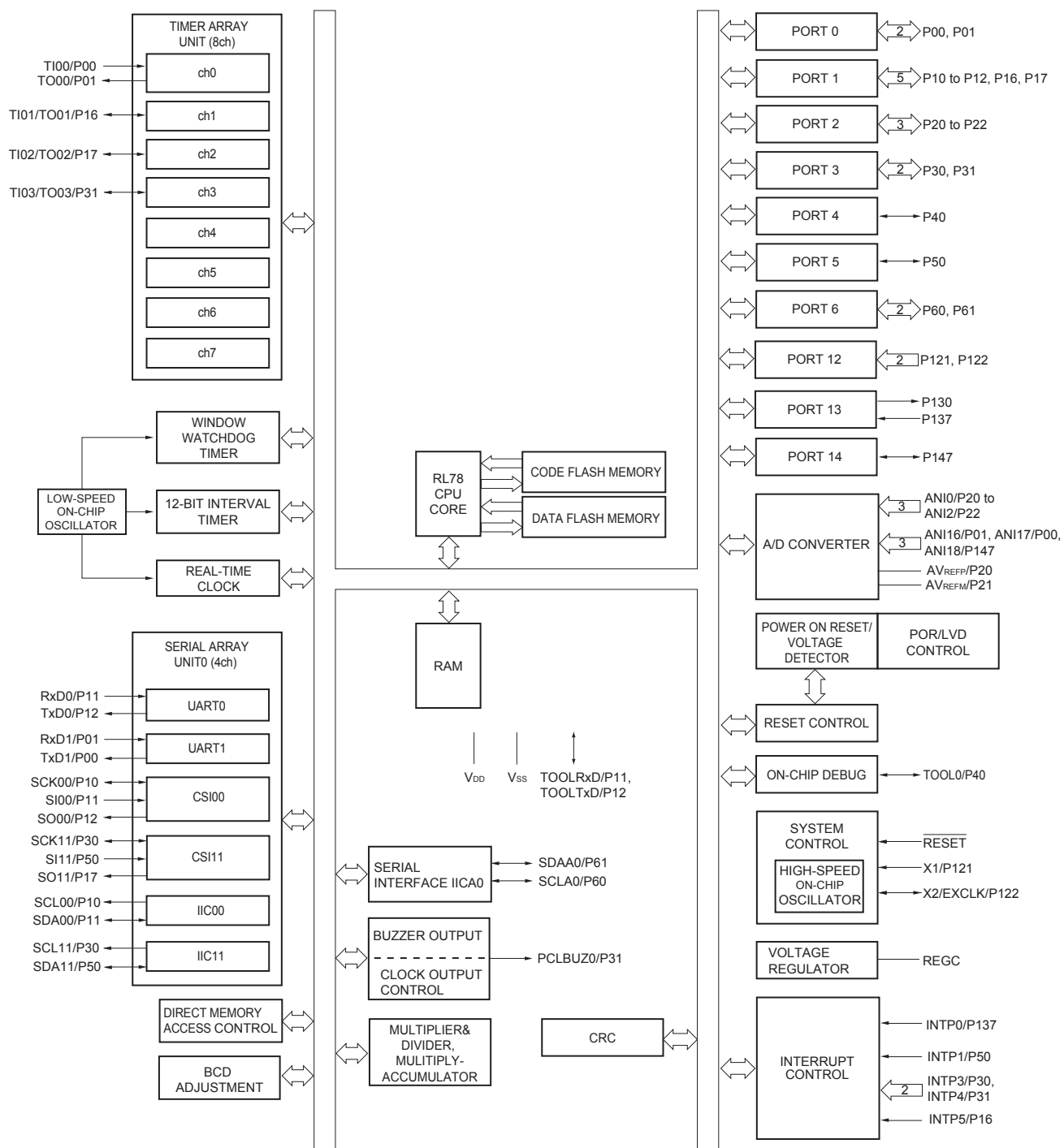
(5/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	Mounted	A	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0, R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0, R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0, R5F100GLAFB#V0 R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0, R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0, R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0, R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0, R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0, R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0, R5F100GLDFB#V0 R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0, R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0, R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0, R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0, R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0, R5F100GHGFB#V0, R5F100GJGFB#V0 R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0, R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0, R5F100GHGFB#X0, R5F100GJGFB#X0
		Not mounted	A	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0, R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0, R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0, R5F101GLAFB#V0 R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0, R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0, R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0, R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0, R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0, R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0, R5F101GLDFB#V0 R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0, R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0, R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0, R5F101GLDFB#X0

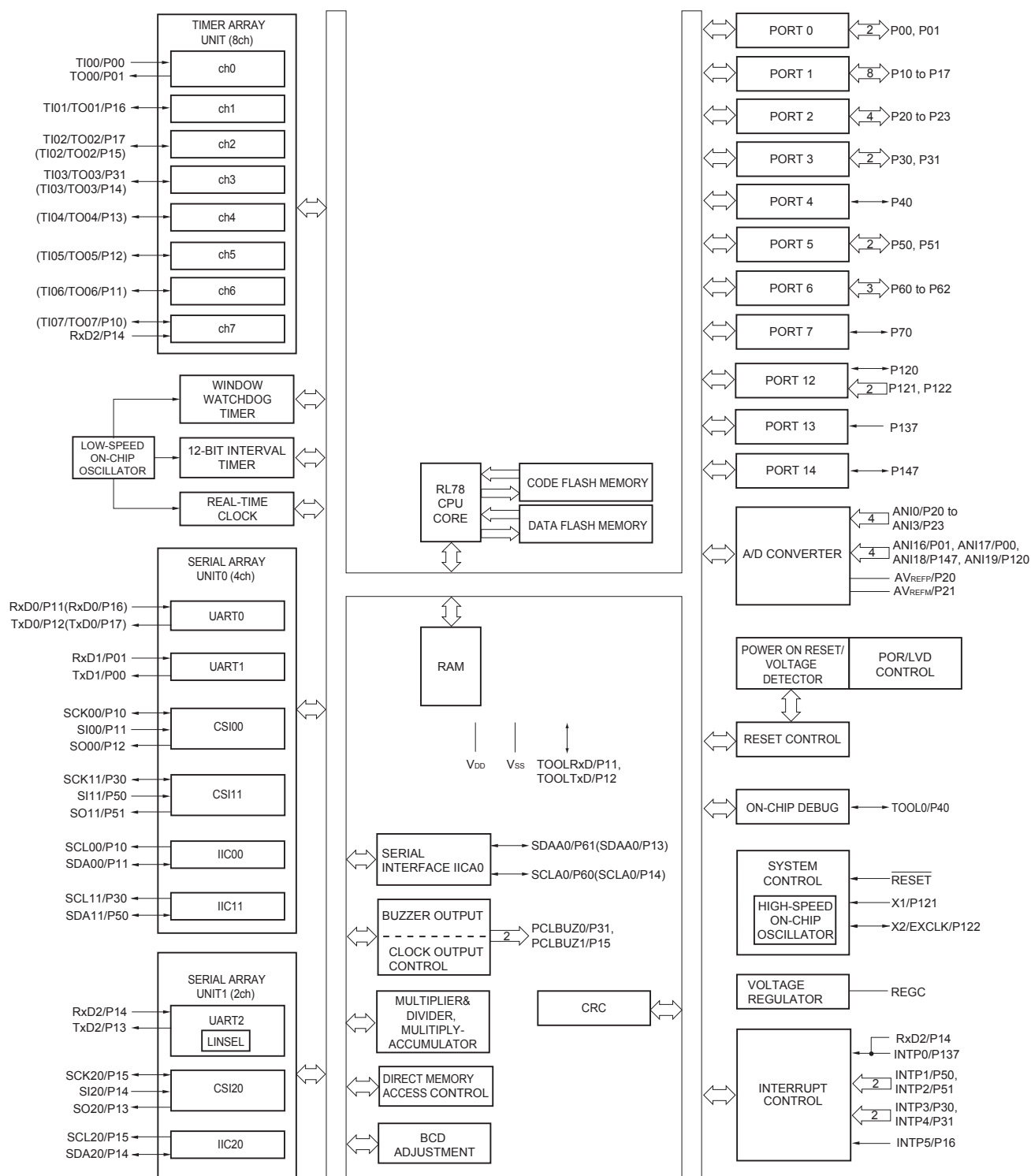
Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.5.3 25-pin products



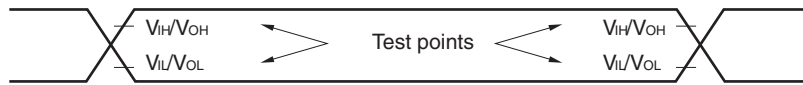
1.5.5 32-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ E_{VDD0} = E_{VDD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = E_{VSS0} = E_{VSS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate ^{Note 1}		2.4 V ≤ E _{VDD0} ≤ 5.5 V		f _{MCK} /6 ^{Note 2}		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}		5.3		1.3		0.6	Mbps
		1.8 V ≤ E _{VDD0} ≤ 5.5 V		f _{MCK} /6 ^{Note 2}		f _{MCK} /6		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}		5.3		1.3		0.6	Mbps
		1.7 V ≤ E _{VDD0} ≤ 5.5 V		f _{MCK} /6 ^{Note 2}		f _{MCK} /6 ^{Note 2}		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}		5.3		1.3		0.6	Mbps
		1.6 V ≤ E _{VDD0} ≤ 5.5 V	—			f _{MCK} /6 ^{Note 2}		f _{MCK} /6	bps
		Theoretical value of the maximum transfer rate f _{MCK} = f _{CLK} ^{Note 3}	—			1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when E_{VDD0} < V_{DD}.

2.4 V ≤ E_{VDD0} < 2.7 V : MAX. 2.6 Mbps

1.8 V ≤ E_{VDD0} < 2.4 V : MAX. 1.3 Mbps

1.6 V ≤ E_{VDD0} < 1.8 V : MAX. 0.6 Mbps

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

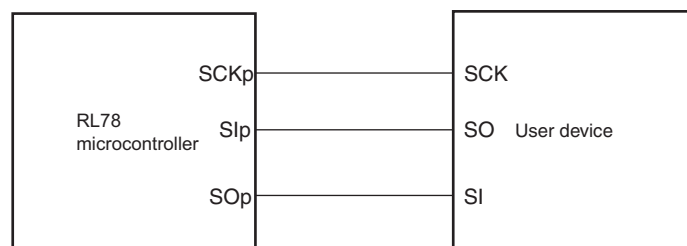
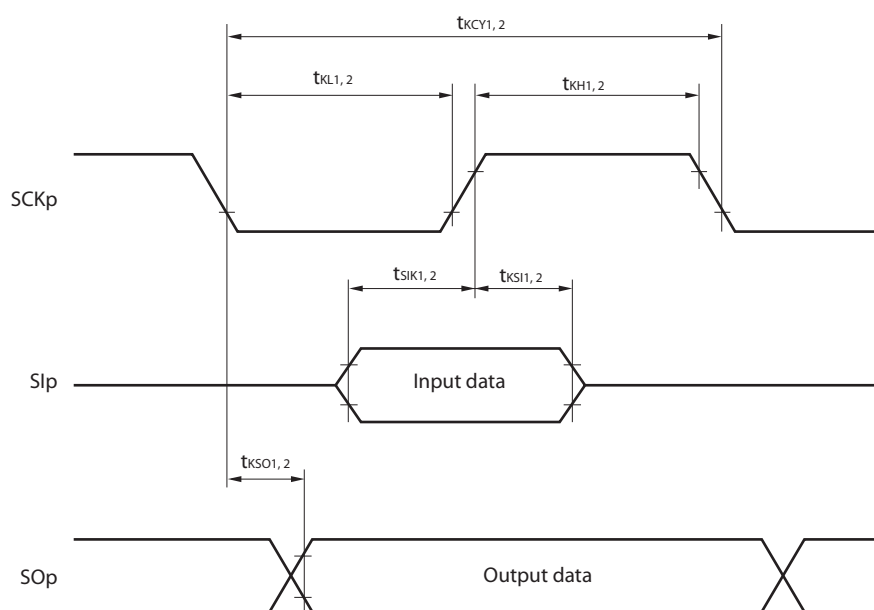
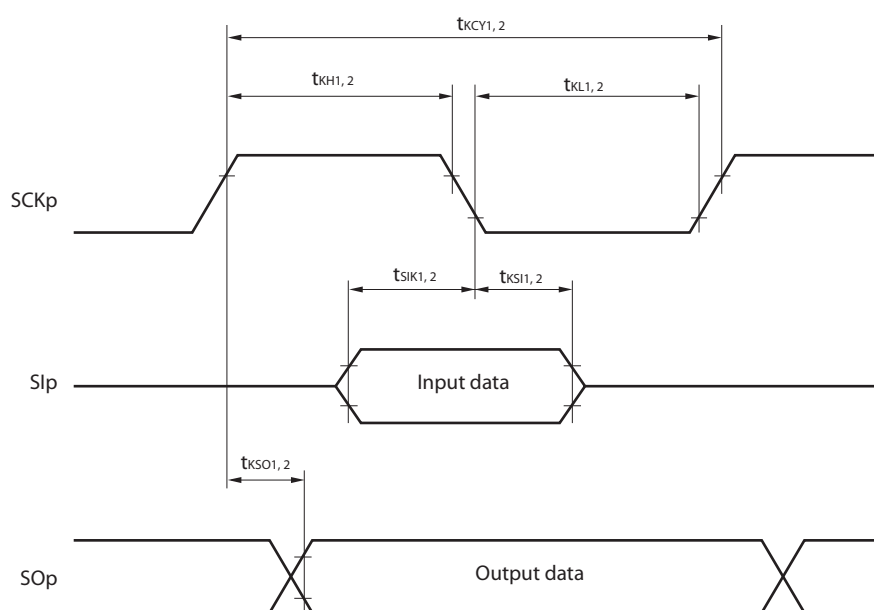
HS (high-speed main) mode: 32 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)

LV (low-voltage main) mode: 4 MHz (1.6 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

CSI mode connection diagram (during communication at same potential)**CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)****CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)**

- Remarks**
1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)
 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
5. Use it with EV_{DD0} ≥ V_b.
6. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

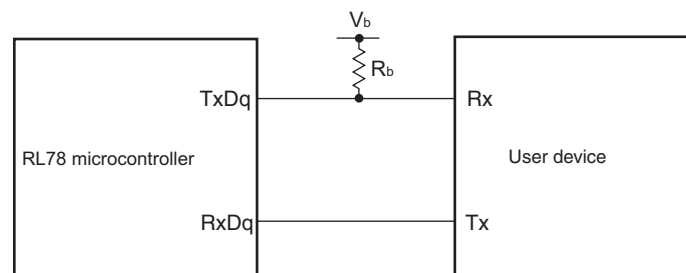
$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

7. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the Rx_{Dq} pin and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the Tx_{Dq} pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



2.6.2 Temperature sensor/internal reference voltage characteristics

(T_A = -40 to $+85^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, HS (high-speed main) mode)

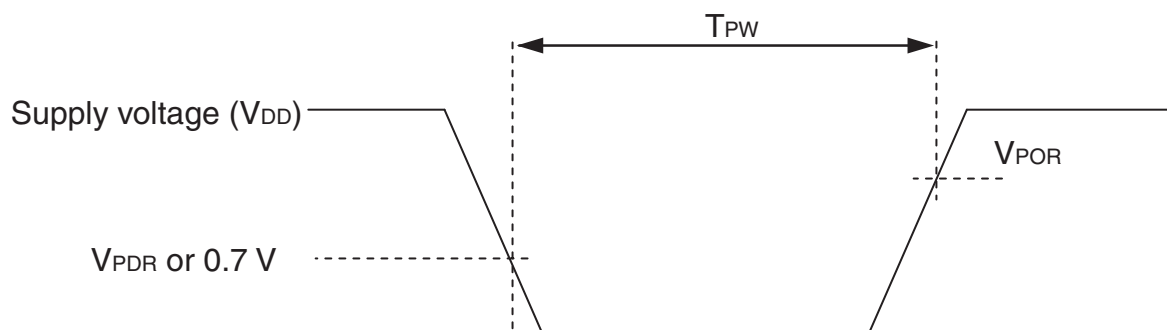
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		-3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	t_{AMP}		5			μs

2.6.3 POR circuit characteristics

(T_A = -40 to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V_{POR}	Power supply rise time	1.47	1.51	1.55	V
	V_{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T_{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR} . This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.5 Power supply voltage rising slope characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

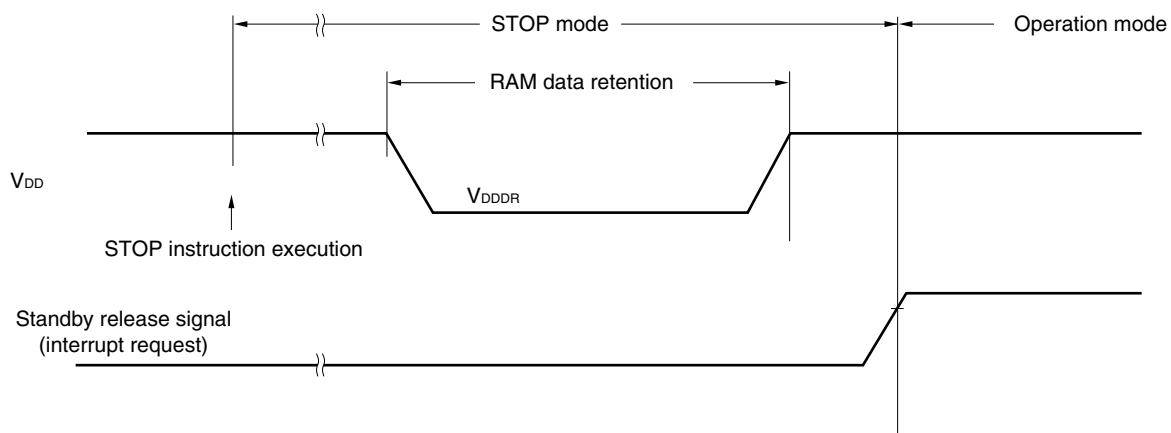
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

($T_A = -40$ to $+85^\circ\text{C}$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_x) ^{Note}	Ceramic resonator/ crystal resonator	$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	1.0		20.0	MHz
		$2.4\text{ V} \leq V_{DD} < 2.7\text{ V}$	1.0		16.0	MHz
XT1 clock oscillation frequency (f_x) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

3.2.2 On-chip oscillator characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency ^{Notes 1, 2}	f_{IH}			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to $+85^\circ\text{C}$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-1.0		$+1.0$	%
		-40 to -20°C	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-1.5		$+1.5$	%
		$+85$ to $+105^\circ\text{C}$	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	-2.0		$+2.0$	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		$+15$	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

(T_A = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (1/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	I _{OH1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$		-3.0 ^{Note 2}	mA
		Total of P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145 (When duty $\leq 70\%$ ^{Note 3})	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$		-30.0	mA
			$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$		-10.0	mA
			$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 2.7\text{ V}$		-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty $\leq 70\%$ ^{Note 3})	$4.0\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$		-30.0	mA
			$2.7\text{ V} \leq \text{EV}_{\text{DD}0} < 4.0\text{ V}$		-19.0	mA
			$2.4\text{ V} \leq \text{EV}_{\text{DD}0} < 2.7\text{ V}$		-10.0	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$2.4\text{ V} \leq \text{EV}_{\text{DD}0} \leq 5.5\text{ V}$		-60.0	mA
	I _{OH2}	Per pin for P20 to P27, P150 to P156	$2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$		-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})	$2.4\text{ V} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$		-1.5	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

2. Do not exceed the total current value.

3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor $> 70\%$ the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(I_{\text{OH}} \times 0.7)/(n \times 0.01)$

<Example> Where $n = 80\%$ and $I_{\text{OH}} = -10.0\text{ mA}$

$$\text{Total output current of pins} = (-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7\text{ mA}$$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD0} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = 0\text{ V}$) (1/2)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	$f_{IH} = 32\text{ MHz}$ Note 3	Basic operation	$V_{DD} = 5.0\text{ V}$		2.1		mA
						$V_{DD} = 3.0\text{ V}$		2.1		mA
					Normal operation	$V_{DD} = 5.0\text{ V}$		4.6	7.5	mA
						$V_{DD} = 3.0\text{ V}$		4.6	7.5	mA
				$f_{IH} = 24\text{ MHz}$ Note 3	Normal operation	$V_{DD} = 5.0\text{ V}$		3.7	5.8	mA
						$V_{DD} = 3.0\text{ V}$		3.7	5.8	mA
				$f_{IH} = 16\text{ MHz}$ Note 3	Normal operation	$V_{DD} = 5.0\text{ V}$		2.7	4.2	mA
						$V_{DD} = 3.0\text{ V}$		2.7	4.2	mA
			HS (high-speed main) mode Note 5	$f_{MX} = 20\text{ MHz}$ Note 2, $V_{DD} = 5.0\text{ V}$	Normal operation	Square wave input		3.0	4.9	mA
						Resonator connection		3.2	5.0	mA
				$f_{MX} = 20\text{ MHz}$ Note 2, $V_{DD} = 3.0\text{ V}$	Normal operation	Square wave input		3.0	4.9	mA
						Resonator connection		3.2	5.0	mA
				$f_{MX} = 10\text{ MHz}$ Note 2, $V_{DD} = 5.0\text{ V}$	Normal operation	Square wave input		1.9	2.9	mA
						Resonator connection		1.9	2.9	mA
				$f_{MX} = 10\text{ MHz}$ Note 2, $V_{DD} = 3.0\text{ V}$	Normal operation	Square wave input		1.9	2.9	mA
						Resonator connection		1.9	2.9	mA
		Subsystem clock operation		$f_{SUB} = 32.768\text{ kHz}$ Note 4 $T_A = -40^\circ\text{C}$	Normal operation	Square wave input		4.1	4.9	μA
						Resonator connection		4.2	5.0	μA
				$f_{SUB} = 32.768\text{ kHz}$ Note 4 $T_A = +25^\circ\text{C}$	Normal operation	Square wave input		4.1	4.9	μA
						Resonator connection		4.2	5.0	μA
				$f_{SUB} = 32.768\text{ kHz}$ Note 4 $T_A = +50^\circ\text{C}$	Normal operation	Square wave input		4.2	5.5	μA
						Resonator connection		4.3	5.6	μA
				$f_{SUB} = 32.768\text{ kHz}$ Note 4 $T_A = +70^\circ\text{C}$	Normal operation	Square wave input		4.3	6.3	μA
						Resonator connection		4.4	6.4	μA
				$f_{SUB} = 32.768\text{ kHz}$ Note 4 $T_A = +85^\circ\text{C}$	Normal operation	Square wave input		4.6	7.7	μA
						Resonator connection		4.7	7.8	μA
				$f_{SUB} = 32.768\text{ kHz}$ Note 4 $T_A = +105^\circ\text{C}$	Normal operation	Square wave input		6.9	19.7	μA
						Resonator connection		7.0	19.8	μA

(Notes and Remarks are listed on the next page.)

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

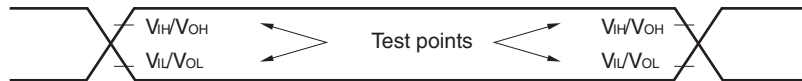
(TA = -40 to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \leq \text{V}_{\text{DD}} \leq 5.5\text{ V}$, $\text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0\text{ V}$) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	I _{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	3.40	mA	
					V _{DD} = 3.0 V		0.62	3.40	mA	
				f _{IH} = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		0.50	2.70	mA	
					V _{DD} = 3.0 V		0.50	2.70	mA	
				f _{IH} = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		0.44	1.90	mA	
					V _{DD} = 3.0 V		0.44	1.90	mA	
				HS (high-speed main) mode Note 7	f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
					f _{MX} = 20 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.31	2.10	mA
						Resonator connection		0.48	2.20	mA
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V		Square wave input		0.21	1.10	mA	
					Resonator connection		0.28	1.20	mA	
			Subsystem clock operation		f _{SUB} = 32.768 kHz ^{Note 5} T _A = −40°C	Square wave input		0.28	0.61	μA
						Resonator connection		0.47	0.80	μA
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +25°C	Square wave input		0.34	0.61	μA	
					Resonator connection		0.53	0.80	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +50°C	Square wave input		0.41	2.30	μA	
					Resonator connection		0.60	2.49	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +70°C	Square wave input		0.64	4.03	μA	
					Resonator connection		0.83	4.22	μA	
				f _{SUB} = 32.768 kHz ^{Note 5} T _A = +85°C	Square wave input		1.09	8.04	μA	
					Resonator connection		1.28	8.23	μA	
			f _{SUB} = 32.768 kHz ^{Note 5} T _A = +105°C	Square wave input		5.50	41.00	μA		
				Resonator connection		5.50	41.00	μA		
	I _{DD3} ^{Note 6}	STOP mode ^{Note 8}	T _A = −40°C					0.19	0.52	μA
			T _A = +25°C					0.25	0.52	μA
			T _A = +50°C					0.32	2.21	μA
			T _A = +70°C					0.55	3.94	μA
			T _A = +85°C					1.00	7.95	μA
			T _A = +105°C					5.00	40.00	μA

(Notes and Remarks are listed on the next page.)

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq E_{VDD0} = E_{VDD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = E_{VSS0} = E_{VSS1} = 0\text{ V}$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate ^{Note 1}		Theoretical value of the maximum transfer rate $f_{CLK} = 32\text{ MHz}$, $f_{MCK} = f_{CLK}$		$f_{MCK}/12$ ^{Note 2}	bps
				2.6	Mbps

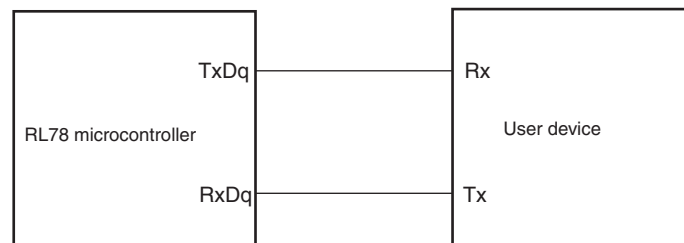
Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

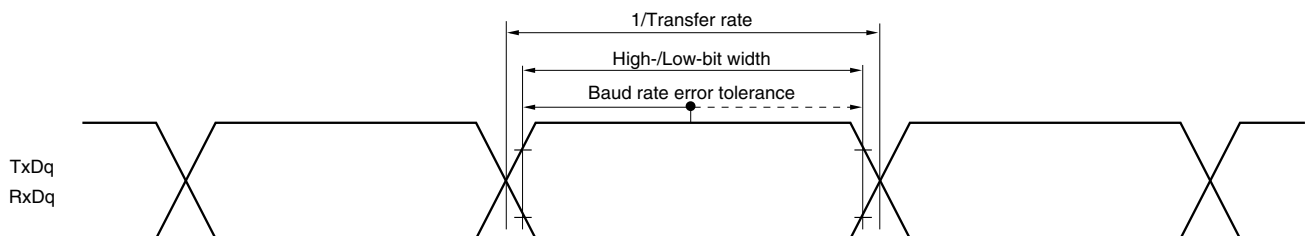
$2.4\text{ V} \leq E_{VDD0} < 2.7\text{ V}$: MAX. 1.3 Mbps

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. f_{MCK} : Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$)**

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		400 ^{Note 1}	kHz
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		400 ^{Note 1}	kHz
		$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$		100 ^{Note 1}	kHz
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$		100 ^{Note 1}	kHz
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$		100 ^{Note 1}	kHz
Hold time when SCLr = "L"	t_{LOW}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	1200		ns
		$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	4600		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	4600		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	4650		ns
Hold time when SCLr = "H"	t_{HIGH}	$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	620		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 50\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	500		ns
		$4.0\text{ V} \leq EV_{DD0} \leq 5.5\text{ V}$, $2.7\text{ V} \leq V_b \leq 4.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.8\text{ k}\Omega$	2700		ns
		$2.7\text{ V} \leq EV_{DD0} < 4.0\text{ V}$, $2.3\text{ V} \leq V_b \leq 2.7\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 2.7\text{ k}\Omega$	2400		ns
		$2.4\text{ V} \leq EV_{DD0} < 3.3\text{ V}$, $1.6\text{ V} \leq V_b \leq 2.0\text{ V}$, $C_b = 100\text{ pF}$, $R_b = 5.5\text{ k}\Omega$	1830		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(2) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (–) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin : ANI16 to ANI26

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} , Reference voltage (–) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 5.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin : ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 3.5	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}$ Notes 3, 4	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.0	LSB
Analog input voltage	V _{AIN}	ANI16 to ANI26	0		AV_{REFP} and EV_{DD0}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

4. When $AV_{REFP} < EV_{DD0} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (–) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (–) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI26	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error ^{Note 1}	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI26		0		EV_{DD0}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} ^{Note 3}			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} ^{Note 3}			V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

- (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (–) = $AV_{REFM}/ANI1$ (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{BGR} ^{Note 3}, Reference voltage (–) = AV_{REFM} ^{Note 4} = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8			bit
Conversion time	t_{CONV}	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	E _{ZS}	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error ^{Note 1}	ILE	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Differential linearity error ^{Note 1}	DLE	8-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 1.0	LSB
Analog input voltage	V_{AIN}			0		V_{BGR} ^{Note 3}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

2. This value is indicated as a ratio (%FSR) to the full-scale value.

3. Refer to **3.6.2 Temperature sensor/internal reference voltage characteristics**.

4. When reference voltage (–) = V_{SS} , the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (–) = AV_{REFM} .

Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (–) = AV_{REFM} .

3.6.2 Temperature sensor/internal reference voltage characteristics

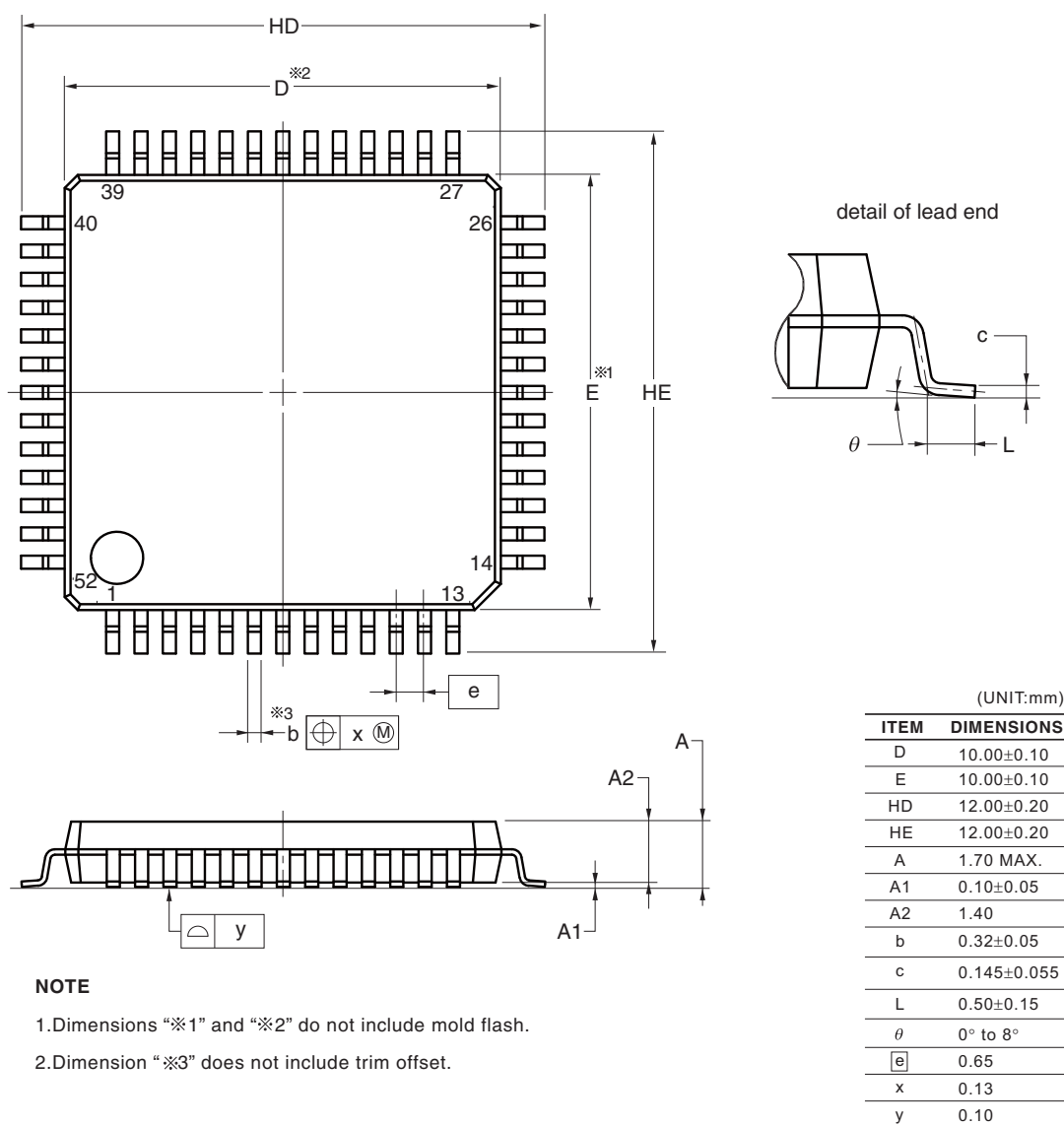
($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V_{TMPS25}	Setting ADS register = 80H, $T_A = +25^\circ\text{C}$		1.05		V
Internal reference voltage	V_{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	F_{VTMPS}	Temperature sensor that depends on the temperature		–3.6		mV/ $^\circ\text{C}$
Operation stabilization wait time	t_{AMP}		5			μs

4.10 52-pin Products

R5F100JCAFA, R5F100JDFA, R5F100JEFA, R5F100JFAFA, R5F100JGAFA, R5F100JHAFA, R5F100JJFA, R5F100JKFA, R5F100JLAFA
 R5F101JCAFA, R5F101JDFA, R5F101JEFA, R5F101JFAFA, R5F101JGAFA, R5F101JHAFA, R5F101JJFA, R5F101JKFA, R5F101JLAFA
 R5F100JCDA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JGDFA, R5F100JHDA, R5F100JDDFA, R5F100JKDA, R5F100JLDA
 R5F101JCDA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JGDFA, R5F101JHDA, R5F101JDDFA, R5F101JKDA, R5F101JLDA
 R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3

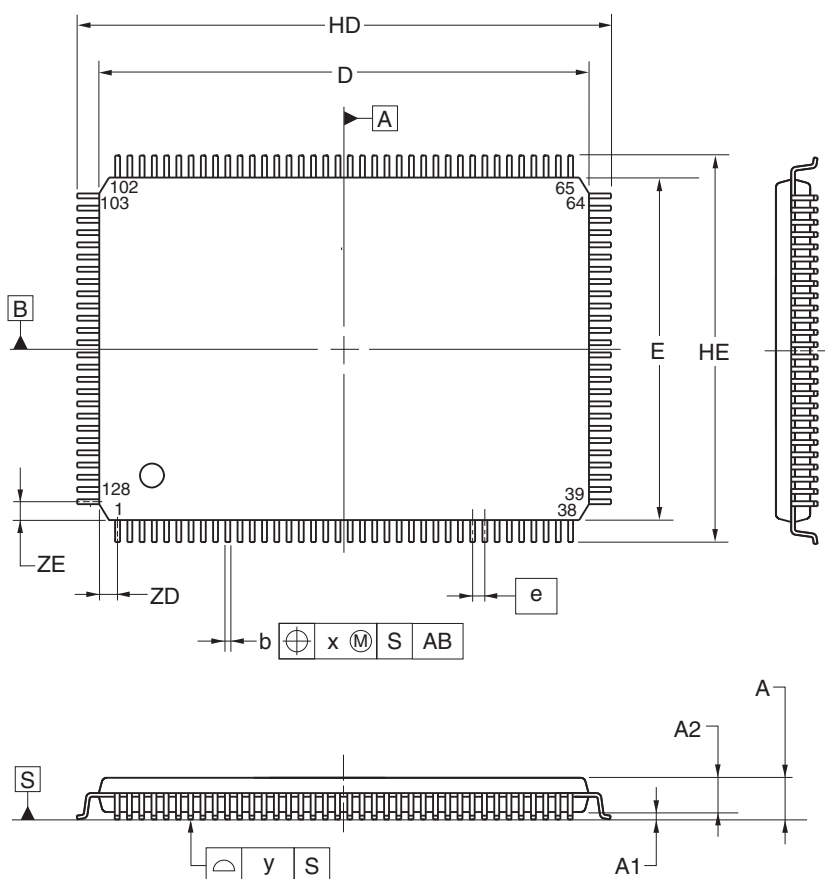


© 2012 Renesas Electronics Corporation. All rights reserved.

4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB
 R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB
 R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB
 R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	0.145 ^{+0.055} _{-0.045}
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	3° ^{+5°} _{-3°}
e	0.50
x	0.08
y	0.08
ZD	0.75
ZE	0.75